



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800

Group Art Unit: 2825

Examiner: C. Lee

In re Application of:

H. WATANABE et al.

Serial No.: 09/320,271

Filed: May 27, 1999

For: SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF

AMENDMENT

Commission for Patents
Washington, D. C. 20231

September 4, 2001

Sir:

In response to the Office Action dated April 30, 2001, please amend the above- identified application as follows:

IN THE CLAIMS:

Please cancel non-elected claims 14-20 without prejudice or disclaimer.

Please amend claim 1 as follows:

1. (Twice Amended) A fabrication method of a semiconductor device comprising the steps of:
- forming a first insulation layer over a substrate,
 - introducing impurities into said first insulation layer,
 - forming a trench in said first insulation layer, and
 - embedding and forming a first conductive layer in said trench.